## INFORMATION REPORT INFORMATION REPORT

#### CENTRAL INTELLIGENCE AGENCY

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SUBJECT	Development and Production of Electronic Tubes and Diodes	DATE DISTR.	ZO MAY 1959	
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#### DEVELOF ENT AND PRODUCTION OF ELECTRONIC TUBES AND DIODES

October/November 1958

2 silicon diodes (heavy duty)

Use: for extra heavy-duty voltage rectifiers

Developed: for the NVX (National Peoples Army)

completed about Oct/Nov 1958

at VED RFT Work fuer Fernmeldewesen (OSW), Berlin-

Or erschoeneweide

Production: for the NVA, small series

Reginning Oct/Nov 1958

at VEB RYT Work fuer Fernmeldewesen (OSW), Berlin-

Oberschoeneweide .

model produced Nov 1958

Fax peak inverse volts: 220 v

Max operating volts: 80 v with capacitive load

160 w with ohmic load

Max rectified current: ~1.2 amp

Max beak forward current's 6 amp

Western equivalent type: similar to Intermetal types OY 6042 and 6043

Remarks: The performance data of the model lie between those of the

two equivalents. The max rectified current of the model and the peak

forward current are, however, higher than in the equivalents. The

dimensions of the equivalents have been duplicated approximately, the

mechanical desirn of the model, however, is different and primitive in

some places. The insulating disk of the Intermetal types are of first-class

micanite: in the GDR types they are of synthetic-resin bonded-paper

sheet (Hartpapier).

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Further development: In Oct/Nov 58, work was in progress at VEB RFT
Work fuer Fernneldewesen on the development of about 8 types of silicon
diodes for operating voltages of 60-600 volts and inverse voltages of
70-750 v.

#### Electronic Transmitter Tubes and Ministure Tubes

December 1958

- √ 1. special subminiature tube (U<sub>a</sub>-60 ♥) ······
- 2. special subministure tube ( = 80,v)
- 1/3. special ministure tube (Ug 72 mg Ig 3.5 mm)
- 4. special miniature tube (Ug 72 Vg I 2 mm)
- /5. special miniature tube (U 52 ♥)
- √ 6. subministure tube (v = 100 v)
- 7. 2 transmitter tube 829 B

The color markings of the top of the tobe gives the veltage class.

Two subministure tubes, special, for use in cecillating circuits up to 1,200 Mc and in output stages up to 300 Mc of transmitters for the NVA (National Peoples Army).

Developed for NVA; development completed about November 1958 at VEB RFT Work fuer Fernmeldevesen (CSW), Berlin-Cherecheenswelde

Production presumably for the NVA, beginning Nov/Dec 1958 at VEB RFT Werk fuer Fernmeldsweeen, CSM, Berlin-Oberschoensweide; model produced December 1958.

I 60 ma

U 60 v

U 2 60 v

U 3 -4.5 v

No known equivalent Western type.

The internal capacitances of the tube are especially low in order that the tube can be used for the largest possible frequency range.

Two special subminiature tubes for use in oscillator circuits up to 1,000 Mc or in output of driver stages up to 250 Me of transmitters for the NVA.

Developed for the NVA about November 1958 by VEB RFT Werk fuer Fernmeldewesen (CSW), Perlin-Oberschoeneweide.

Production presumably for the NVA, beginning Nov/Dec 1958, by ugn Rum Werk fuer Fernmeldewesen. Model produced December 1958:

Technical data: 
$$U_{f}$$
: 1.3  $\forall$   $U_{g}$ 1: -5.2  $\forall$   $I_{f}$ : 55 ma  $I_{a}$ : 9 ma  $U_{a}$ : 80  $\forall$  S: 0.9 ma/ $\forall$   $U_{g}$ 2: 80  $\forall$ 

No known Western equivalent type.

Two special miniature tubes for use in two-way radiotelephone sets.

Development by VER RFT Werk fuer Fernmeldewesen (OSW), Berlin-

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Operschoeneweide; contractor and completion date of development not known.

Production by VEB RFT Werk fuer Fernmeldewesen for unknown contractor; delivery address to VEB RFT Funkwerk Koempenick; model produced December 1958; production in small series.

#### Technical data: (limits)

U.	1.3 v		U <sub>g</sub> 1	<b>-7 ▼</b>
T <sub>f</sub>	50 <b>m</b>	-1.	I	3.5 m
U	72 ▼ .		<b>S</b> -	0.7 m/v
U 2	72 ▼		N	350 ==

- 2.6 micromicrofared
- c 3.2 mioromicrofered

Nó known equivalent Western type.

Remarks: The sets in which the tubes are to be used eperate on a wavelength of 1.5 meters (200 Mc), thus special emphasis was put on obtaining the lowest possible internal capacitance.

Two special miniature tubes for use in two-way radiotelephone sets.

Developed at VEB RFT Work fuer Fernmeldewesen; production at VEB

RFT Work fuer Fernmeldewesen for unknown contractor; delivery to VEB

RFT Funkwork Koepenick; production in small series, amount not known;

model produced December 1958.

Remarks: The sets in which the tubes are to be used operate on a wavelength of 1.5 meters (200 Mo) thus special diphesis during development was put on obtaining the lowest possible internal separatance.

Two special miniature tubes for use in two-way radiotelephone sets.

Developed by VEB RFT Work fuer Fernmeldewesen, Berlin-Oberschoensweide.

Production by VEB RFT Work fuer Fernmeldewesen for unknown contractor;

delivery address: VEB RFT Funkwork Kospenick; unknown ensunt of production,
small series; model produced December 1955.

Technical data: U 1.3 v
I 100 ma

Ua 52 v

Ug<sup>2</sup> 52 v

I 3.2 ma

8 2.3 ma/v

N 530 ms

c 4 micromicrofared

ca 0.008 micromicrofared

No known equivalent Western type.

Remark: The sets in which the tubes are to be used operate on a wavelength of 1.5 meters (200 No) thus special emphasis during development was put on obtaining the lowest possible internal capacitance.

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Two subministure tubes for use as output pentode for portable whf transmitter-receiver sets for the National Posples Army.

Development on contract for the NVA, not yet eandluded, at VEB RFT Work fuer Fernmeldewsen.

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Model produced December 1958, special manufacture for laboratory research and tests.

Technical data: U 1.3 V

I 120 ma

U 100 V

U 2 100 V

U k -7 V

I 12 ma

8 2.2 ma/v

A new type of subministure series. The contractor insists on the delivery of tubes with these ratings.

Two transmitter tubes, 829/B, special manufacture for stationary and mobile transmitters of average and high output.

Developed at VEB RFT Work fuer Ferumeldesseem, Berlin-Gerecheensweide, (improvement)

Produced at VEB RFT Work fuer Permildenesen en contract for the NVA and for export. Hodel produced December 1958. Production in small

Technical data: max plate voltage 650 v

negative control grid bias -130 v

screen grid voltage 250 v

heater voltage 6.3 v

Equivalent Western type: precumably an improved model of the USA army tube 829, used in mobile transmitters and obtained by the USER through lend-lesse.

Remarks: The transmitter tube deviates semewhat in performance stings from the old model of the same designation and has different

•

electrodes and different anode cooling.

For the purpose of modulating the 829 B transmitter tube, the 6 SL 7 (octal series) driver tube is used together with it. This driver tube is given the same designation in the tube lists of the US armed forces, and has been copied for years by RFT Werk fuer Fernmeldsweet for empert to the USSR. The East German tube deviates semewhat from the US tube with respect to electrical data.

In centrast to the US designs, the GER tubes (829 N and 6 SL 7 GF, and other all-glass designs), the JAN type designation and mammfacturer are not etched into the glass envelope, but in the total base.

### Electrical Diodes and Transistors (EFT-Factories)

#### December 1958

(original model and descriptive meterial)

- 1. Universal diode (-  $U_{\rm p} = 100 \text{ y}$ )
- 2. Universal diode (-U = 105 v)
- 3. Special diede (- $\overline{v}_{D} = 70 \text{ v}$ )
- 4. Subministure diode (-U = 100 v)
- 5. Subministere diede (-0 = 80 v)
- 6. Transistor
- 7. Special solder

## Shifting of Development and Production of Spensisters

In the fourth quarter of 1958, the shifting of the development and production of transistors to VER EFF Funkmerk Eschlede (Thuringle) began. Funkwerk Koellede is supposed to be the parent factory for transistor manufacture. Technical installations and equipment were shifted

from factories in the Berlin area to Koelleda, and scientists and engineers have been transferred there also.

These measures are based on the fact that the production of important semiconductor components had to be removed from the Berlin area because of the tense political situation of Berlin. It is possible that this is only a pretext for purposes of propagatida designed to make the people involved amenable to the move. (Generally, the people engaged in this work rebel at the idea of leaving the Berlin area.)

The professional people of VER RFT Funkwerk Berlin-Kespenick work closely together with Funkwerk Koelleda, since the laboratory tests on the manufactured products of Funkwerk Koelleda are for the most part conducted at Funkwerk Koepenick.

New laboratory facilities are being built at VEB Penkwerk Koelleda.

The laboratory experiments there are still being conducted at 20 deg Cent room temperature in a machine testing shop, whereas intermeticual standards call for a room temperature of 25 deg Cent.

Development of a new portable two-way radiotelephone see

The development on this set was completed in December 1958 at VEB
RET Funkwork Kospenick. The set is allegedly a copy, with several improvements, of the KL 9 set used in the West German army.

The set is designed for entrying to head a terrored on the back ("knapsack-suitcase" design). It sperates to a terrored on 1.5 many, has a completely transistorised power pack, and uses 10 channels (the EL 9 set uses only 3 channels.).

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Two universal dictes; development feelings

production at VER RFT Funkwerk Koelleds; model produced Dec 1958

A universal all-glass diode, the strays of which are still quite

Two universal diodes; developed at VEB RFT Funkwork Keelleda; production at VEB RFT Funkwork Keelleda; model produced Dec 1958.

All-glass design.

Two special diodes; developed at VES 197 Funkwerk Reelleda;
production at VES RFT Funkwerk Keelleda; medels produced Des 1958;
production in small series.

Technical data: -U, 70 ▼

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JD (-u<sub>DM max</sub>) 15 ma i<sub>DM</sub> 160 ma i<sub>st</sub> 230 ma

reportat Hode works as an electrical switch.

Two subministure diodes (all-glass) used in small portable whf transmitter-receiver sets, and possibly for control head (Steuerkopf) of special devices. 25X1

Developed presumably for the NVA (National Peoples Army) at VER RFT Funkwerk Koelleda; production in small series (about Mc-95% rejects) begun presumably Nov/Dec 1958 at VER RFT Funkwerk Koelleda; models produced December 1958.

Technical datas -UD 100 v
-UDM 120 v

JD (-UD at 0 v) 60 ma

JD (-UDM max) 18 ma

iDM 160 ma

600 ma

Remarks: The Subministure diods in allegians theigh HAS CEN SAME
limiting data as the universal diods described in Assex 1. For the
manufacture of the subministure diods, first-class material is used
according to especially observed manufacturing methods. The requirement of the same performance as that of the universal diods, with the
smallest dimensions, explains the high master of rejects.

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Two subminiature diodes for use in small portable short-wave (whf) transmitter-receiver sets, primarily in ratio-detector circuits.

Developed presumably for the NVA; developed at VEB HTT Funkwerk Koelleda.

Production begun presumably NOV/Dec 1958 at VEB RFT Funkwerk
Koelleda; model produced December 1958; small series.

Technical data: -U<sub>D</sub> 80 v

-U<sub>D</sub>N 110 v

JD (-U<sub>D</sub> at 0 v) 60 ms

JD (-U<sub>DN</sub> max) 12 ms

1DN 120 ms

Equivalent Western types OR 85 (with different design)

Remarks: Silicon diodes of the same type for a Seminative country of minus 60 to plus 150 deg Cent were in development at the Eff.

Pankwerk Koellede in December 1958.

One transistor (with high amplification factor) for use in a audio-frequency amplifier in A- or B-clustic and in william rectifier circuits. (Gleichspanningswendler amplication).

Development for Af? ( Office of Technology), tests protected wild 1958 at: either VEB NFT Rechromork, Manhaus, or

VER RFT- Work Erfort

VER RFT Funkwerk Koellede

Production also at one of the three above plants; preduction model

# SECREI

wie hresumably in December 1958, small series.

Technical data: U 8

Ū<sub>cp</sub> 16 ▼

Jc 2,000 ma

J 2,000 ma

Nc 6,000 me

T max plus 45 deg Cent
(as voltage rectifier)

Equivalent Western type: presumably TKD GFT 2005

Remarks: The transister was tested at the laboratory of

VEB RFT Funkwerk Koepenick for the NVA (National Peoples Army),
but it was not produced there.

One material sample of special solder for soldering connections to semiconductor components.

Development finished in 1958 at VEB RFT Punkwerk Kospenick, on pontract for VEB RFT Punkwerk Kospenick.

Production begun 1958 on contract for VEB EFF Punknesk Ecopeniak.

Technical data: especially sensitive to heat, flows at only 150 deg

Centigrade 7, with high strength and otherwise good properties.

Eq.ivalent Western type: on hand.

